First principle investigation on thermoelectric properties of transition metal dichalcogenides: Beyond rigid band model

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Two-dimensional direct band-gap transition-metal dichalcogenides (TMDC) with chemical composition MX_2 (M=Mo or W and X=S or Se) have led to a growing interest in the last decade. For instance, in the field of nanoelectronic, significant accomplishments have been done in the development of MoS₂ based transistors.

We have investigated the thermoelectric properties (electrical conductivity, Seebeck coefficient and power factor) of single layer TMDC on the basis of ab initio quantum transport using Landauer Büttiker formalism (see Figure 1). The often used rigid band model is compared to realistic doping, namely substitution and adsorption, it is found that several important physical insights governing the transport are missing in this approximation. The rigid band model appears to clearly overestimate the thermoelectic efficiency, hampering its relevance for thermoelectric studies. Substitution doping by chloride or phosphorus leads to poor power factor due to drastic changes of the pristine band structure. In contrast, adsorption doping by alkalies (Li, Na, K and Rb) favors larger power factor (see Figure 2).

Thanks to the landauer formalism, a realistic treatment of the disorder dopants induced by the is also investigated and reveals that CI doping leads to very short localization length of 3.5 nm whilst K comes with micrometer length scale. The Anderson localization phenomenon in thermoeletric properties of single layer transition metal dichalcogenides definitely comes out as a main issue.

Figures



Figure 1. Schematic representation of the system within the Landauer formalism.



Figure 2. Power factor for MoS_2 with 3 different dopants: K, Li and Cl, as well as the rigid band calculation.